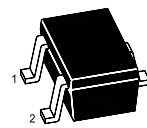
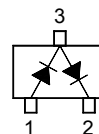


MMBD204SEW

Silicon Epitaxial Planar Switching Diode

Applications

- Ultra high speed switching



SOT-323 Plastic Package
Marking Code: **A7**

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	20	V
Reverse Voltage	V_R	20	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current (Single)	I_{FM}	200	mA
Non-repetitive Peak Forward Surge Current ($t = 1\ \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_d	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\ \text{mA}$	V_F	1	V
Reverse Current at $V_R = 15\ \text{V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 6\ \text{V}$, $f = 1\ \text{MHz}$	C_T	4	pF

